

SCREEN Semiconductor Solutions Co., Ltd.

Accelerated innovation through strategic collaboration:
a view from an equipment supplier

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SCREEN Semiconductor Solutions Co., Ltd.
CTO

March 1, 2018



1 **Company outline and Product Line-up**

2 **LETI collaboration → A long History**

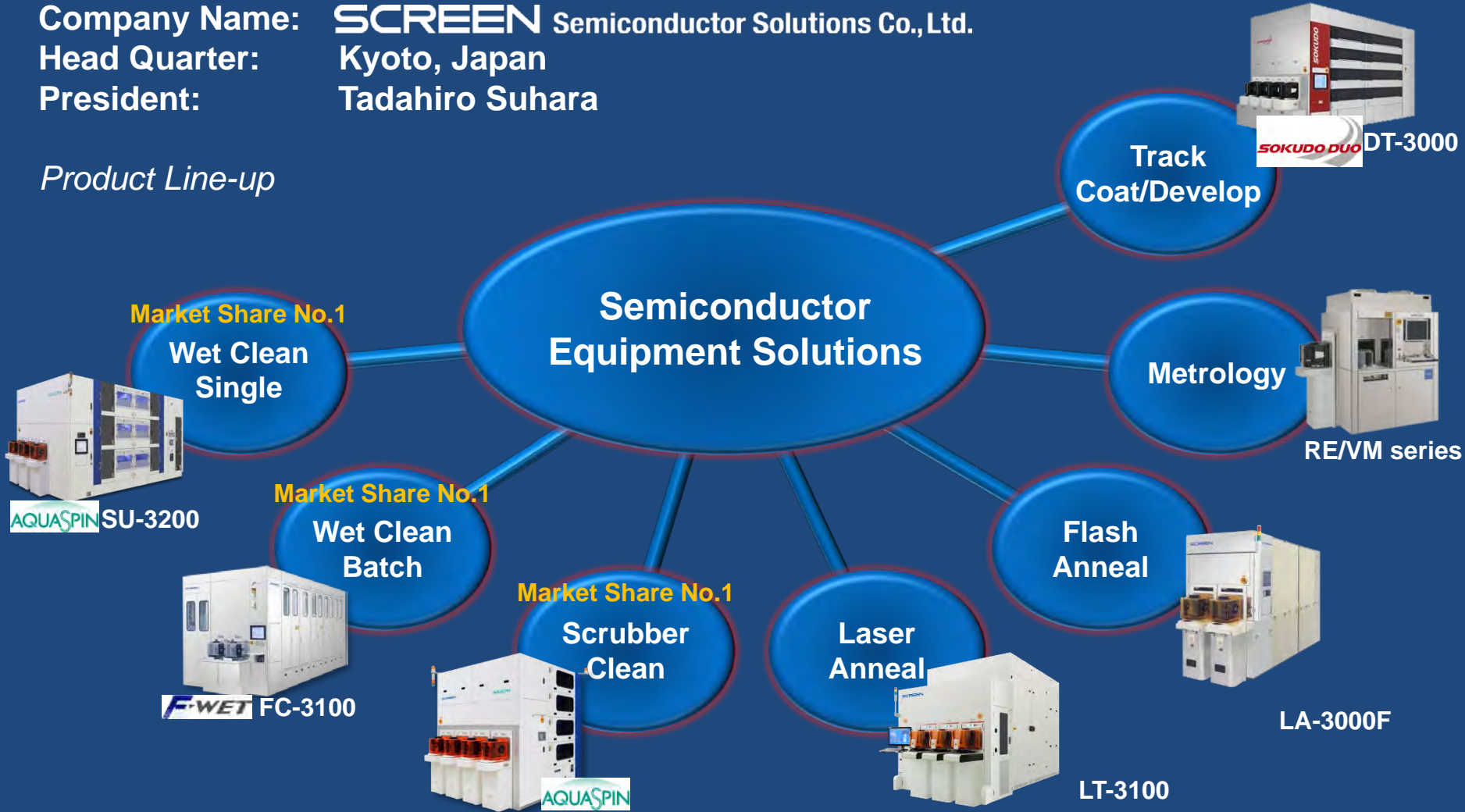
3 **Wet Clean & Litho. Track highlights**

4 **Focus on Laser anneal collaboration**

5 **Conclusion**

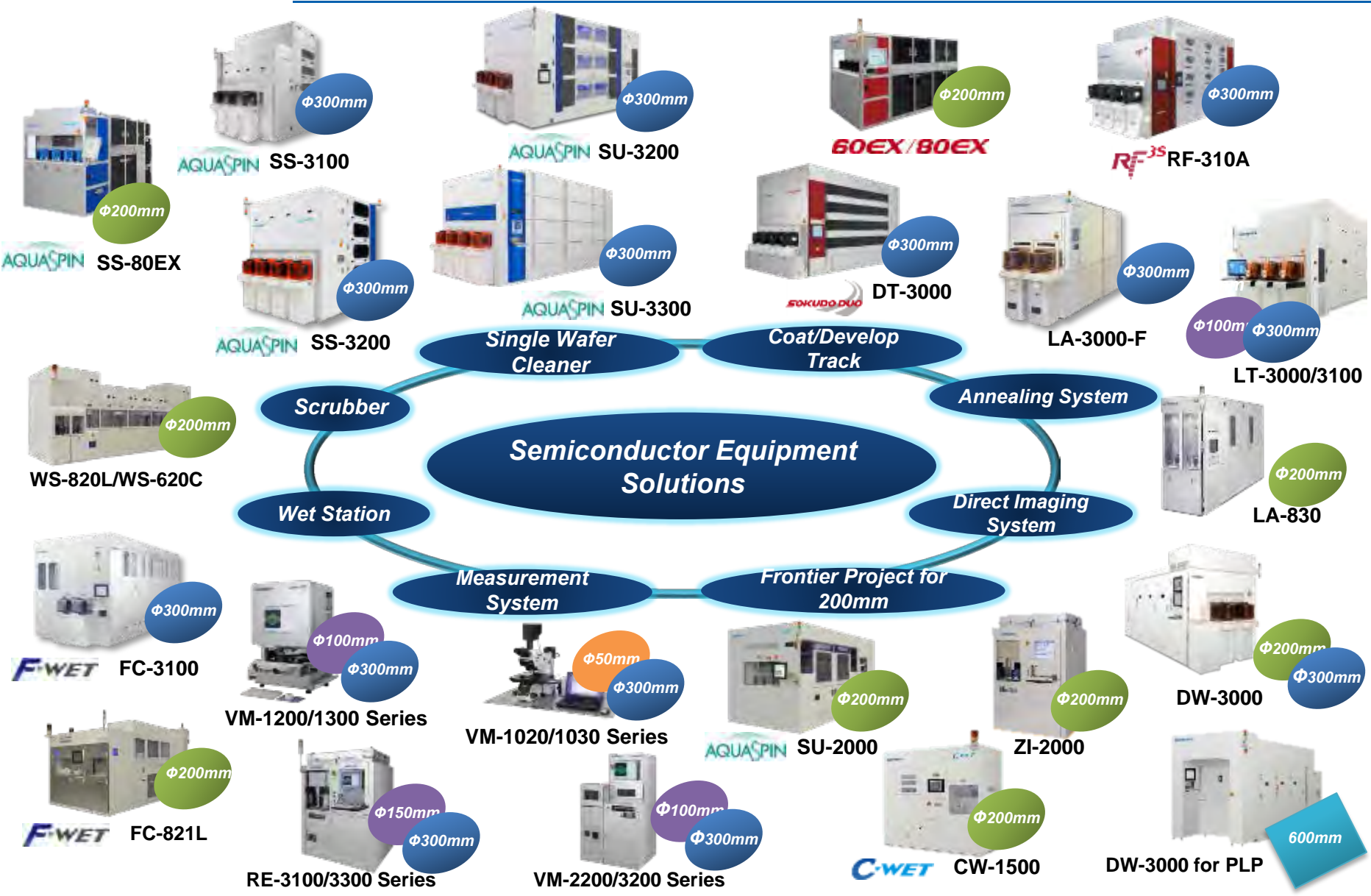
Company Name: **SCREEN** Semiconductor Solutions Co.,Ltd.
Head Quarter: Kyoto, Japan
President: Tadahiro Suhara

Product Line-up



Source: Gartner, April 2015

Product Line-up



Office and Plants Locations



**Process Technology Center
(Hikone Plant)**



**Fab. FC-1・FC-2
(Hikone Plant)**

Headquarter



Taga Plant

**WHITE CANVAS RAKUSAI
(Rakusai Site)**



**Global Training Center
(Yasu Plant)**



PRESS RELEASE

SCREEN SEMICONDUCTOR SOLUTIONS AND LETI EXPAND COLLABORATION TO COVER LASER ANNEAL TECHNOLOGY

KYOTO, Japan and GRENOBLE, France – Dec. 1st, 2016 – "SCREEN Semiconductor Solutions Co., Ltd. (SCREEN) and Leti, a CEA Tech institute, today announced they have stepped up their collaboration with the installation at Leti's site of a nanosecond-scale UV laser anneal LT-3100 system to be delivered by Laser Systems and Solutions of Europe (LASSE), SCREEN's subsidiary based in France"

"The introduction of SCREEN's nanosecond-scale UV laser anneal tool in Leti's leading-edge, pre-industrial equipment infrastructure will open new innovation opportunities for current and future technology being developed on site," said Leti CEO Marie Semerla. "With SOI, CoolCube™ and nanowire technologies development, we are facing increased challenges in developing new material property and ultra-thin-film modification with minimal thermal impact. Leveraging the LT-3100 system will enable solutions for technology breakthroughs that will eventually lead to the development of practical demonstrators for industry."

"Following a long history of successful joint developments with Leti, we are very excited by the opportunity to bring our laser technology to Leti's ecosystem to support 'More than Moore', IoT and future innovation technology requirements," said Tadahiro Suhara, president of SCREEN Semiconductor Solutions. "In addition to the collaboration activities, we will use Leti's state-of-the-art infrastructure to operate our LASSE European demo lab, giving our customers unprecedented demonstration infrastructure capability. We expect to showcase the innovation value that our nanosecond-scale UV laser-equipment technology and resources bring to advance semiconductor process development in multiple fields of research and development as supported by Leti."

The Laser tool is expected to be fully operational in the first half of 2017 and will support multiple wafer size requirements to meet the different needs of Leti's laboratories.



PRESS RELEASE

SOKUDO Joins CEA-Leti IMAGINE Program to Develop Multiple E-Beam Lithography Process

KYOTO, Japan and GRENOBLE, France – Sept. 16, 2010 – SOKUDO Co., Ltd., the lithography coat/develop track process equipment joint venture company, and CEA-Leti today announced that SOKUDO will join the new industry/research multi-partner program IMAGINE that is developing maskless lithography for IC manufacturing.

The three-year project is led by CEA-Leti, the leading French semiconductor research institute, and also includes semiconductor manufacturers TSMC and STMicroelectronics. It is evaluating a maskless lithography infrastructure and the use of MAPPER Lithography tools for high throughput. The multiple e-beam-lithography program covers a global approach to the technology, including tool assessment, patterning and process integration, data handling, prototyping and cost analysis.

"E-beam has the potential to be a viable technology for many sub-22nm lithography process layers in logic/foundry semiconductor manufacturing," said Tadahiro Suhara, SOKUDO president and CEO. "SOKUDO is taking a comprehensive approach to being prepared for coat/develop track process readiness in multiple sub-22nm lithography technologies, including immersion ArF lithography extensions, EUV and e-beam lithography. The CEA-Leti IMAGINE collaboration brings together a focused effort to enable production-worthy e-beam lithography, including multiple resist manufacturers key to sub-22nm process development."

"We have been working with SOKUDO's RF3 coat-and-develop track system for many years and the IMAGINE program will benefit from the strong knowledge and support of SOKUDO in developing the necessary processes to support maskless technology," said Serge Tedesco, CEA-Leti program manager. "The experience of CEA-Leti in e-beam technology combined with SOKUDO's coat-and-develop track expertise will help secure the necessary process infrastructure for multi e-beam lithography."

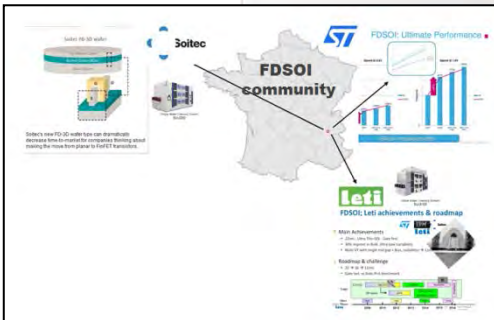
MAPPER Lithography B.V., based in Delft, The Netherlands, makes maskless-lithography machines for the semiconductor industry. It is supporting the IMAGINE project with its massively parallel electron-beam platforms.

MAPPER FLX-1200 E-Beam Lithography



- ◆ **2012: SCREEN engagement via JDP's in FDSOI community.**
(STMicroelectronics, SOITEC, LETI)
- ◆ **2012: Installation of first WET Single Wafer Cleaner SU-3100 for FEOL applications.**
- ◆ **2014: Installation of second WET Single Wafer Cleaner SU-3100 for BEOL applications.**
- ◆ **2015: SCREEN joined European program WAYTOGOFAST.**

Single Wafer Cleaner SU-3100



Single Wafer Cleaner SU-3100



2012

2014

2015



**Article in Solid State Technology from
Laurent Pain, Raluca Tiron, Ludovic
Lattard, Stefan Landis and Cyrille Laviron**

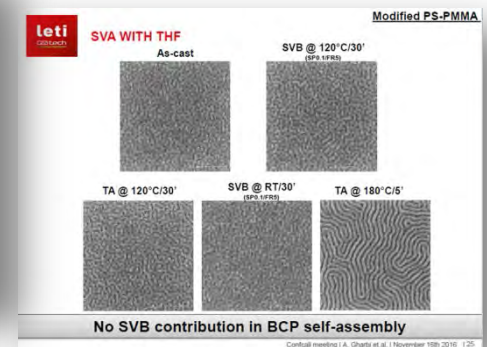
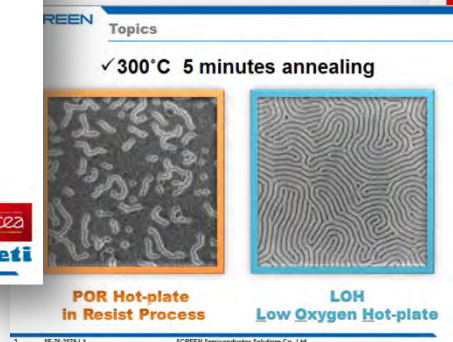
KEY PROJECTS:

1. Leti IDEAL JDA to achieve DSA POR and process yield (CH Via)
2. Leti IMAGINE JDA to achieve E-Beam POR enabling new market
3. Improve Defect /CDU /LWR with new technologies
4. New process development with chemical vendors

◆ SPIE Advanced Lithography 2013~2018

- The potential of block copolymer's directed self-assembly for contact hole shrink and contact multiplication (2013)
- 300mm pilot line DSA contact hole process stability (2014)
- Handling, clamping and alignment evaluation for Multi-beam technology on Matrix1.1 platform (2014)
- Investigation of coat-develop track system for placement error of contact hole shrink process (2016)
- DSA process window extension via controlled atmospheric conditions through accurate defectivity and roughness measurements (2017)
- A track process for solvent annealing of high- χ BCPs (2017)
- **DSA Process Window Expansion by Oxygen Concentration (2018)**

◆ International Symposium on DSA 2015, 2016, 2017





E-Beam Exposure niche market development for rapid prototype IC

Immersion ArF Lithography
NXT:1970Ci Lithocell @ CEA-LETI



FX-1200 E-Beam Exposure Tool

track in-line integration

track in-line integration

LASSE

Laser Systems and Solutions of Europe SAS

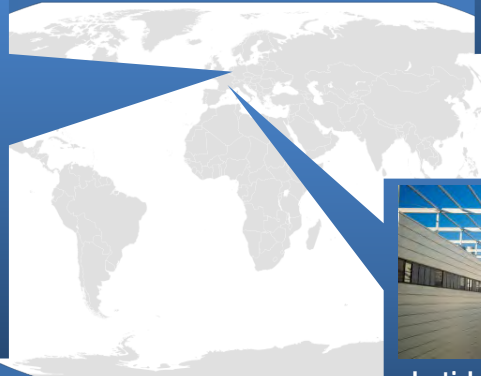
Development and production of Laser Thermal Anneal

Establishment : June, 2014
 President : Tadahiro Suhara

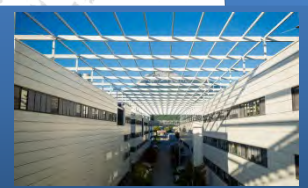
14-38 Rue Alexandre,
 Bldg D F-92230 Gennevilliers,
 France
 Tel : +33-1-41-11-2720



LASSE HQ Factory



SCREEN Process Technology Center



Leti-LASSE Process Development lab

Main product: Laser Annealer

LT-3000/3100

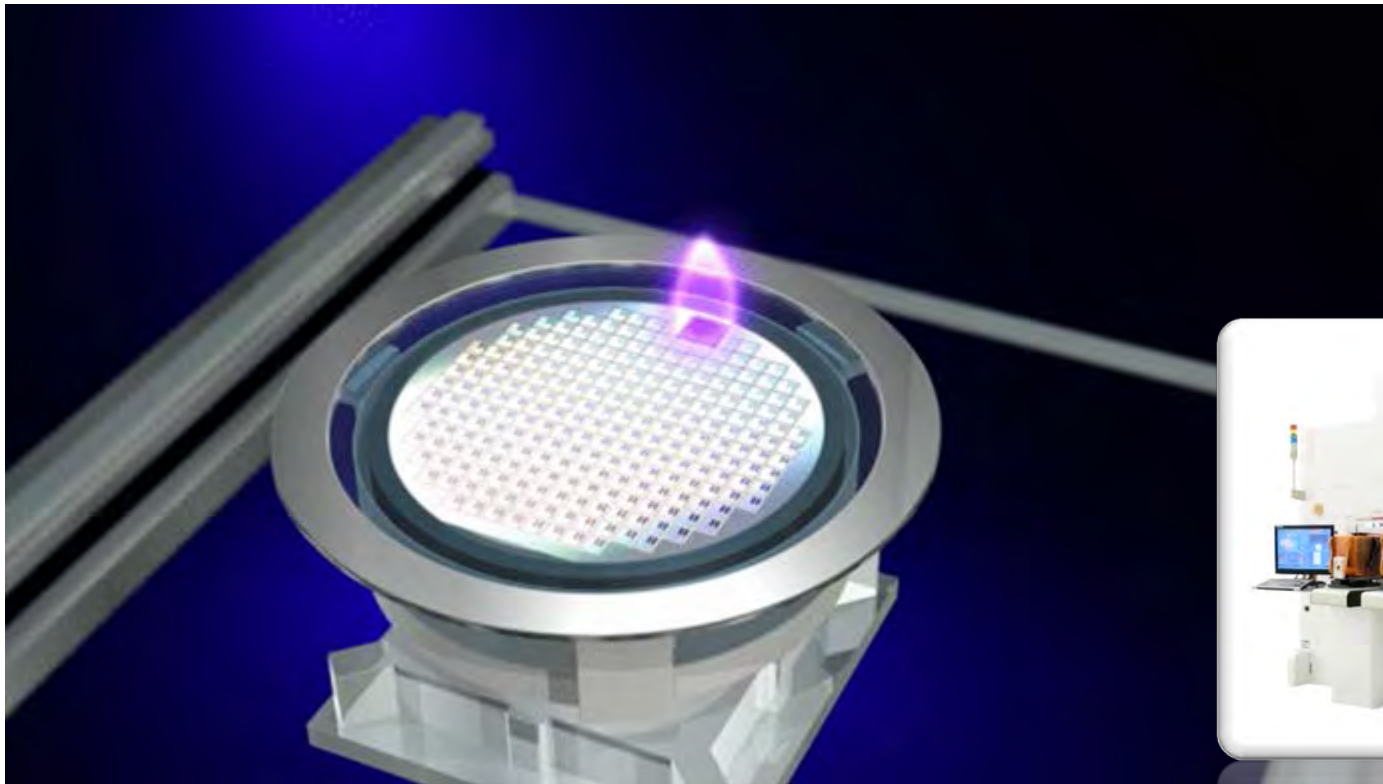


Φ200mm

Φ300mm

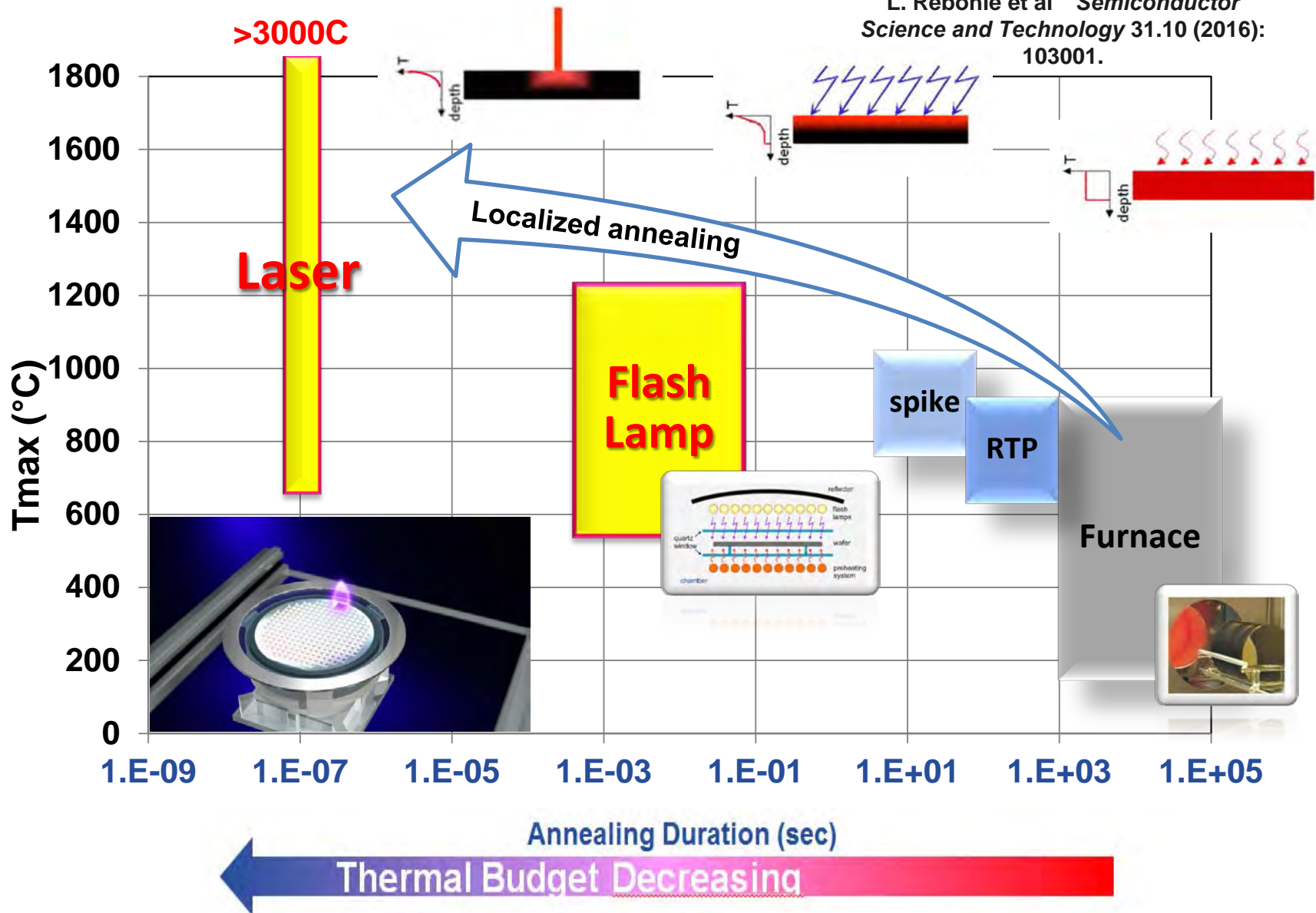
- Ultra-Iow Thermal Budget
 Achieving the highest possible temperature gradient in sub-micro seconds, LT tools are able to anneal fragile substrates without damaging critical device structures.
- Full Device Exposure
 Annealing one die, a group of dies or only the desired region in a single shot, the LT makes it all possible by shaping the beam size to meet process and device requirements without stitching.
- Dopant Activation Control
 Obtaining unprecedented high line and parametric yield levels are only possible with the LT annealing process. By melt-annealing, the dopants are superactivated and the low resistance layer is defect free.

- ◆ The only production proven Melt Laser Anneal Technology
- ◆ High Energy UV pulsed (160 ns) laser for shallow anneal
- ◆ Step & repeat anneal process up to full field size (no stitching)
- ◆ High productivity and modular platform



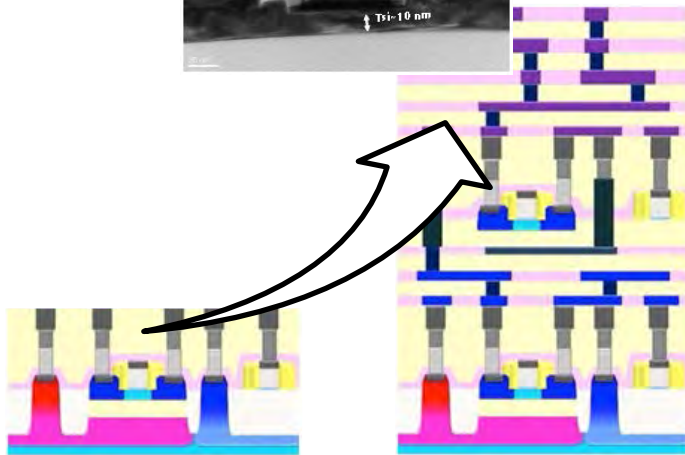
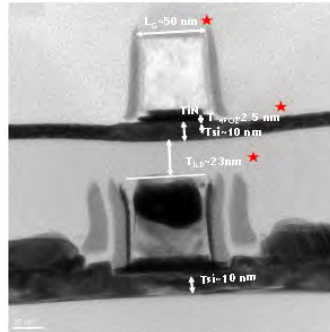
Thermal Annealing Technology Portfolio

L. Rebohle et al " Semiconductor Science and Technology 31.10 (2016): 103001.

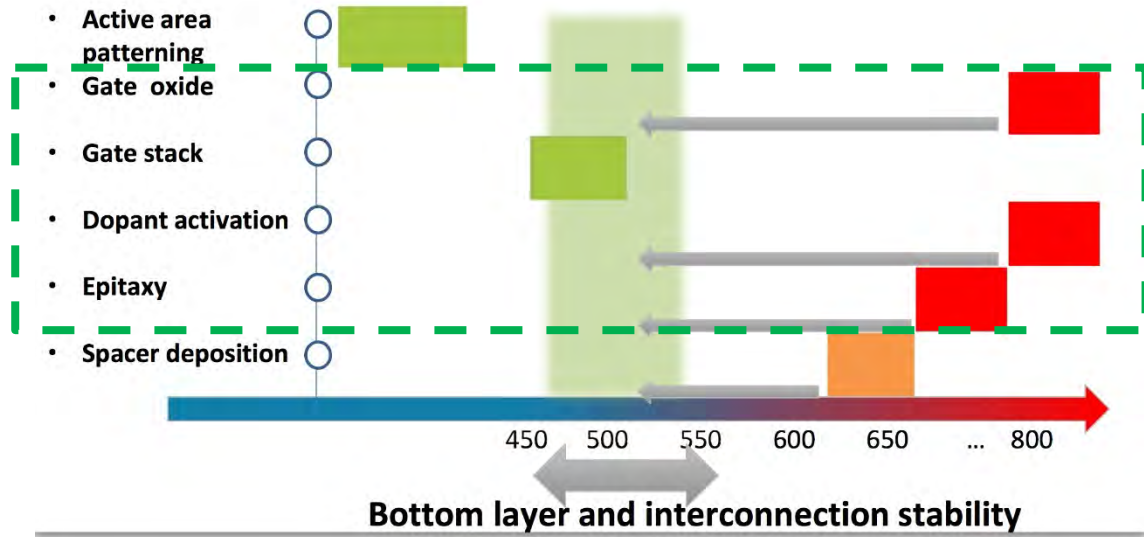


CoolCube® : 3D integration challenges

Candidate application for laser annealing



From Icti CoolCube Program



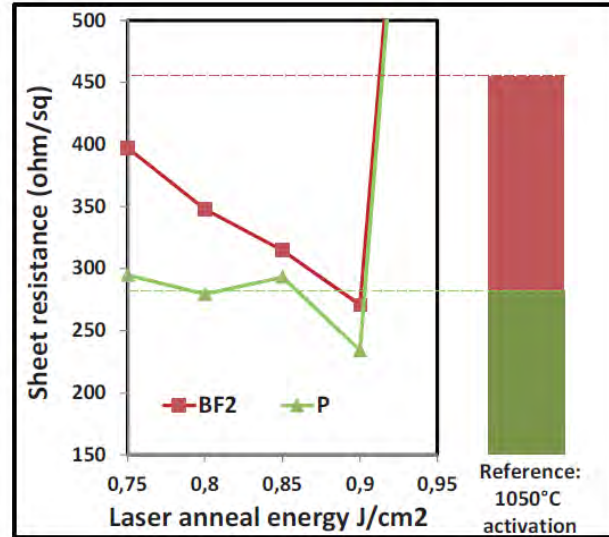
Need for process solution capable of surface localized annealing without affecting buried structure

◆ Ultra localized annealing on top layer:

- Crystallization
- Activation
- Stress engineering

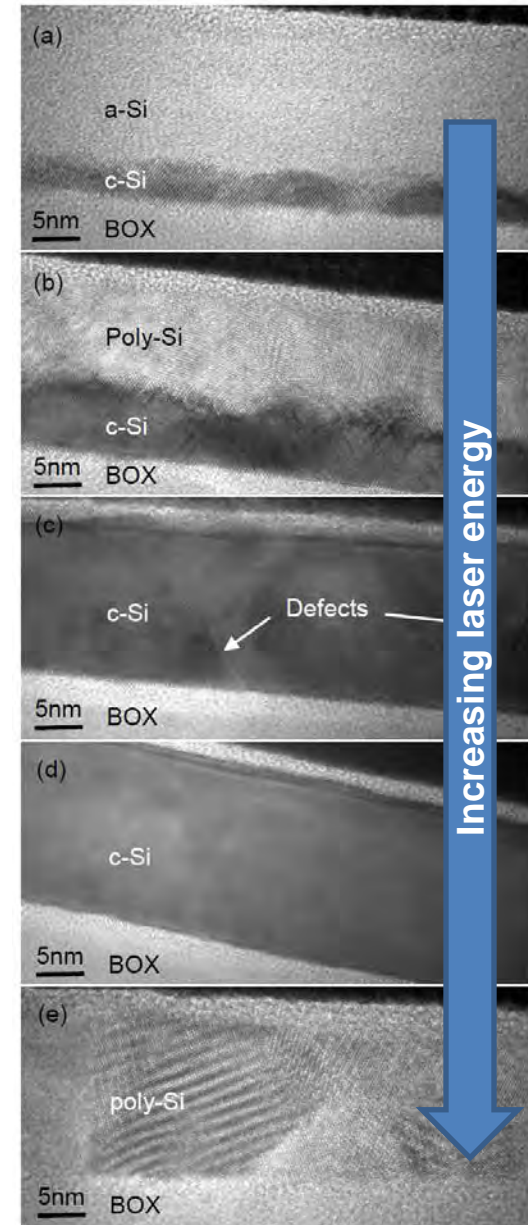


P. Batude et al, VLSI 2011



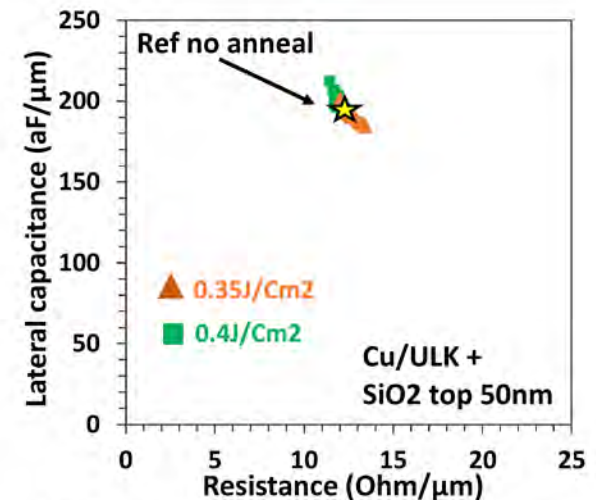
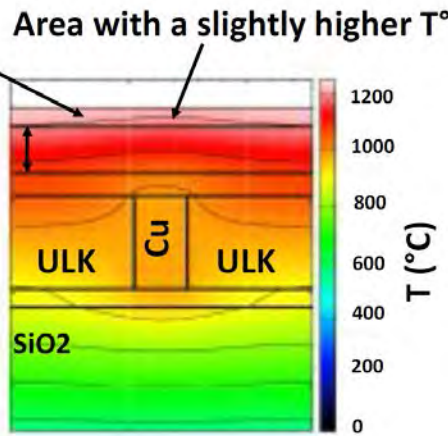
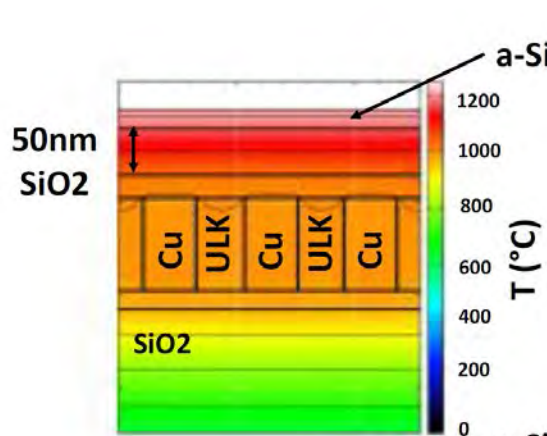
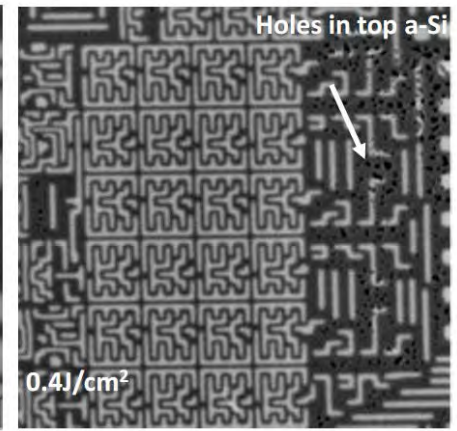
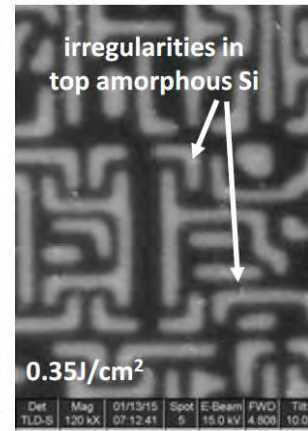
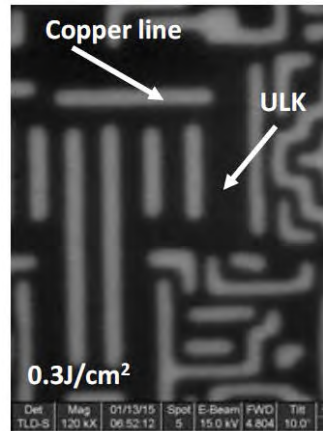
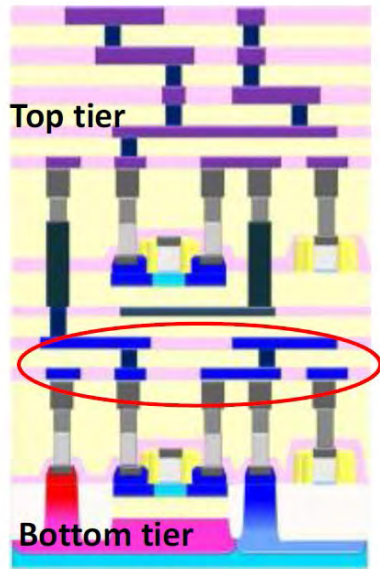
S. Kerdilès et al. in proceeding IWJT 2016

Arsenic junction



Increasing laser energy

Interconnect not degraded at high temperature in nanosecond timescale

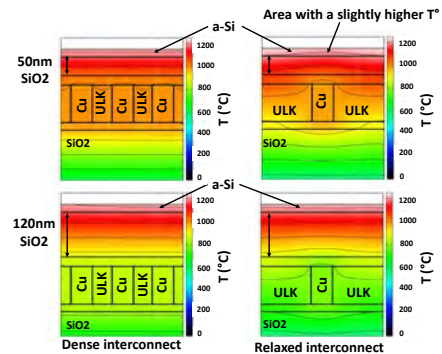
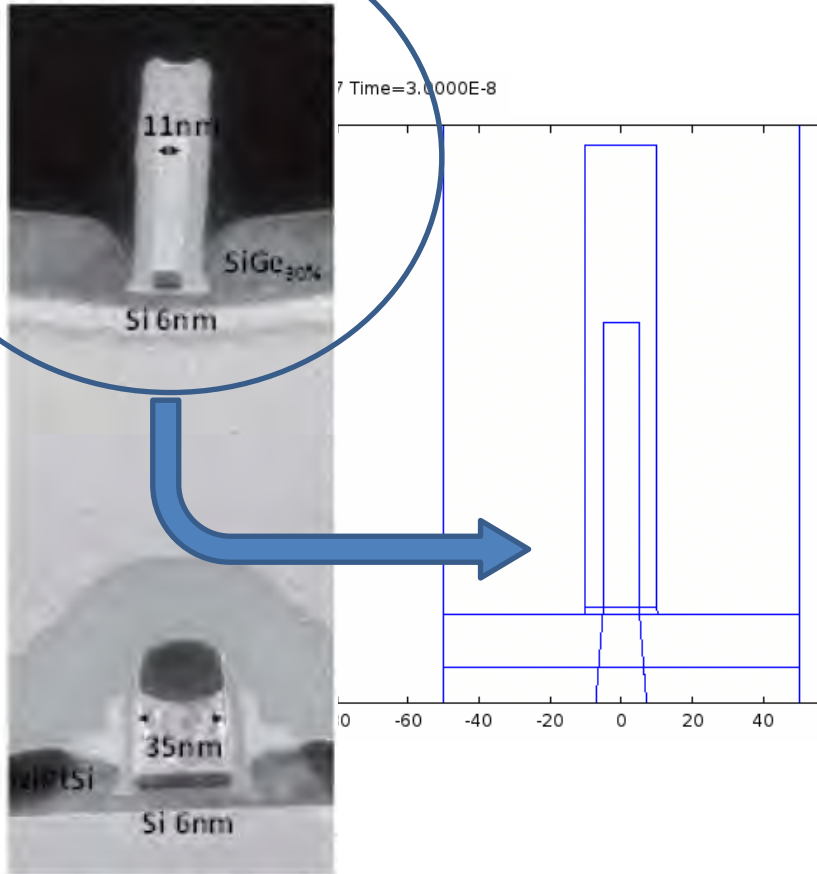


C. Fenouillet S3S 2015 (Leti)

Laser integration supported by LASSE Innovation Booster

Simulating thermal, phases, diffusion dynamics during laser annealing

- ✓ Fully-owned Standalone software
- ✓ Native 3D
- ✓ Collaborating and developing with top academic experts
- ✓ Customer oriented
- ✓ Optimized for LT technology



Accelerated Innovation through Strategic Collaboration

- 1. This is not a nice to have value proposition**
- 2. Build overtime through deep technology exchange**
- 3. Mutually beneficial ⇔ Need to offer Win-Win**
- 4. Benefits our customers with innovation acceleration**

Fit your needs, Fit your future

SCREEN